

IN THE CLAIMS:

Please cancel Claims 1-25 without prejudice to or disclaimer of the subject matter contained therein.

All claims currently in this application, whether amended or not, are being reproduced below for the Examiner's convenience.

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26. (Not Amended) A method of producing a nanostructure comprising an anodized film including a nanohole on a substrate having a surface containing at least one material selected from the group consisting of semiconductors, noble metals, Mn, Fe, Co, Ni, Cu and carbon, said nanoholes passing through said anodized film from the surface of said anodized film to the surface of said substrate, wherein said method comprising the steps of:

(i) forming a film containing aluminum on the substrate having a surface containing at least one material selected from the group consisting of semiconductors, noble metals, Mn, Fe, Co, Ni, Cu and carbon; and

(ii) anodizing said film containing aluminum, wherein in step (ii) the anodization is conducted while monitoring an anodization current and the anodization of said film containing aluminum terminates when a reduction in said anodization current from a steady-state value is detected.

27. (Not Amended) A method of producing a nanostructure according to Claim 26, wherein the anodization terminates when the anodization current is decreased from the steady-state value of 95% or below of the steady-state value.

28. (Not Amended) A method of producing a nanostructure according to Claim 27, wherein an anodization

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voltage applied to said film including aluminum is supplied from the substrate side.

4 29. (Not Amended) A method of producing a nanostructure according to Claim 26, further comprising the step of expanding the diameter of the nanoholes by means of etching, after completion of said anodizing step.

5 30. (Not Amended) A method of producing a nanostructure according to Claim 26, further comprising the step of forming an anodization starting point on the surface of said film including aluminum prior to said anodizing step.

6 31. (Not Amended) A method of producing a nanostructure according to Claim 30, wherein a recessed portion serving as said anodization starting point is formed on said film including aluminum prior to said anodizing step.

7 32. (Not Amended) A method of producing a nanostructure according to Claim 30, further comprising the step of embedding an inclusion into said aluminum oxide nanoholes after said anodizing step.

8 33. (Not Amended) A method of producing a nanostructure according to Claim 32, wherein the embedding of the inclusion is performed by means of electro-deposition.

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9 ~~34~~. (Not Amended) A method of producing a nanostructure according to Claim ~~33~~<sup>8</sup>, wherein the surface of said substrate includes a high-resistance part, and wherein said method further comprises the step of converting said surface at the bottom of the nanohole into a low-resistance surface prior to the electro-deposition.

10 ~~35~~. (Not Amended) A method of producing a nanostructure according to Claim ~~34~~<sup>9</sup>, wherein the surface of said substrate includes a silicon oxide and said surface is etched with an aqueous solution containing hydrofluoric acid or an alkaline aqueous solution.

11 ~~36~~. (Not Amended) A method of producing a carbon nanotube device, comprising the steps of:

forming a film including aluminum on a substrate having a surface including an n-type semiconductor region;

anodizing said film including aluminum over the entire thickness thereof so as to form an anodized film

Ins B1/2 having a nanohole; <sup>B1</sup>

electro-depositing a catalytic fine particle on the surface at the bottom of said nanohole; and

growing carbon nanotubes from said catalytic fine particle in the nanohole.

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